

# CY54FCT827T, CY74FCT827T 10-BIT BUFFERS WITH 3-STATE OUTPUTS

SCCS034A – SEPTEMBER 1994 – REVISED OCTOBER 2001

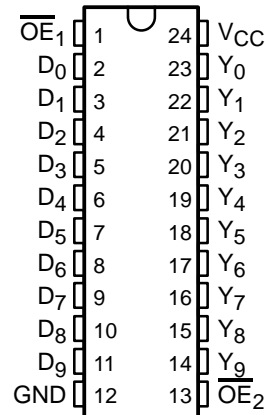
- Function, Pinout, and Drive Compatible With FCT, F, and AM29827 Logic
- Reduced  $V_{OH}$  (Typically = 3.3 V) Versions of Equivalent FCT Functions
- Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics
- $I_{off}$  Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)
- 3-State Outputs
- Matched Rise and Fall Times
- Fully Compatible With TTL Input and Output Logic Levels
- CY54FCT827T
  - 32-mA Output Sink Current
  - 12-mA Output Source Current
- CY74FCT827T
  - 64-mA Output Sink Current
  - 32-mA Output Source Current

## description

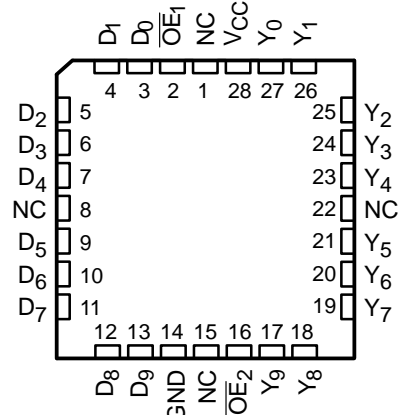
The 'FCT827T devices are 10-bit bus drivers that provide high-performance bus-interface buffering for wide data/address paths or buses carrying parity. The 10-bit buffers have NANDed output enables for maximum control flexibility. The 'FCT827T devices are designed for high-capacitance-load drive capability, while providing low-capacitance bus loading at both inputs and outputs. All outputs are designed for low-capacitance bus loading in the high-impedance state.

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

CY74FCT827T . . . Q OR SO PACKAGE  
(TOP VIEW)



CY74FCT827T . . . L PACKAGE  
(TOP VIEW)



NC – No internal connection



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS  
INSTRUMENTS**

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On products compliant to MIL-PRF-38535, all parameters are tested unless otherwise noted. On all other products, production processing does not necessarily include testing of all parameters.

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T <sub>A</sub>	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QSOP – Q	Tape and reel	4.4	CY74FCT827CTQCT	FCT827C
	SOIC – SO	Tube	4.4	CY74FCT827CTSOC	FCT827C
		Tape and reel	4.4	CY74FCT827CTSOCT	
	QSOP – Q	Tape and reel	8	CY74FCT827ATQCT	FCT827A
	SOIC – SO	Tube	8	CY74FCT827ATSOC	FCT827A
		Tape and reel	8	CY74FCT827ATSOCT	
–55°C to 125°C	LCC – L	Tube	9	CY54FCT827ATLMB	

### FUNCTION TABLE

INPUTS			OUTPUT Y	FUNCTION
$\overline{OE}_1$	$\overline{OE}_2$	D		
L	L	L	L	Transparent
L	L	H	H	
H	X	X	Z	3-state
X	H	X	Z	

[illegible]

NOTE 1: The package thermal impedance is calculated in accordance with JEDEC 51-7.

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**recommended operating conditions (see Note 2)**

		CY54FCT827T			CY74FCT827T			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V <sub>CC</sub>	Supply voltage	4.5	5	5.5	4.75	5	5.25	V
V <sub>IH</sub>	High-level input voltage	2			2			V
V <sub>IL</sub>	Low-level input voltage			0.8			0.8	V
I <sub>OH</sub>	High-level output current			–12			–32	mA
I <sub>OL</sub>	Low-level output current			32			64	mA
T <sub>A</sub>	Operating free-air temperature	–55		125	–40		85	°C

NOTE 2: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation.

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS		CY54FCT827T			CY74FCT827T			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V <sub>IK</sub>	V <sub>CC</sub> = 4.5 V, I <sub>IN</sub> = –18 mA		–0.7		–1.2				V
	V <sub>CC</sub> = 4.75 V, I <sub>IN</sub> = –18 mA					–0.7		–1.2	
V <sub>OH</sub>	V <sub>CC</sub> = 4.5 V, I <sub>OH</sub> = –12 mA		2.4		3.3				V
	V <sub>CC</sub> = 4.75 V	I <sub>OH</sub> = –32 mA				2			
		I <sub>OH</sub> = –15 mA				2.4		3.3	
V <sub>OL</sub>	V <sub>CC</sub> = 4.5 V, I <sub>OL</sub> = 32 mA		0.3		0.55				V
	V <sub>CC</sub> = 4.75 V, I <sub>OL</sub> = 64 mA					0.3		0.55	
V <sub>hys</sub>	All inputs		0.2			0.2			V
I <sub>I</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> = V <sub>CC</sub>				5				μA
	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> = V <sub>CC</sub>							5	
I <sub>IH</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> = 2.7 V				±1				μA
	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> = 2.7 V							±1	
I <sub>IL</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> = 0.5 V				±1				μA
	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> = 0.5 V							±1	
I <sub>OZH</sub>	V <sub>CC</sub> = 5.5 V, V <sub>OUT</sub> = 2.7 V				10				μA
	V <sub>CC</sub> = 5.25 V, V <sub>OUT</sub> = 2.7 V							10	
I <sub>OZL</sub>	V <sub>CC</sub> = 5.5 V, V <sub>OUT</sub> = 0.5 V				–10				μA
	V <sub>CC</sub> = 5.25 V, V <sub>OUT</sub> = 0.5 V							–10	
I <sub>OS</sub> ‡	V <sub>CC</sub> = 5.5 V, V <sub>OUT</sub> = 0 V		–60	–120	–225				mA
	V <sub>CC</sub> = 5.25 V, V <sub>OUT</sub> = 0 V					–60	–120	–225	
I <sub>off</sub>	V <sub>CC</sub> = 0 V, V <sub>OUT</sub> = 4.5 V				±1			±1	μA
I <sub>CC</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> ≤ 0.2 V, V <sub>IN</sub> ≥ V <sub>CC</sub> – 0.2 V		0.1		0.2				mA
	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> ≤ 0.2 V, V <sub>IN</sub> ≥ V <sub>CC</sub> – 0.2 V					0.1		0.2	
ΔI <sub>CC</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> = 3.4 V <sup>§</sup> , f <sub>1</sub> = 0, Outputs open		0.5		2				mA
	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> = 3.4 V <sup>§</sup> , f <sub>1</sub> = 0, Outputs open					0.5		2	

† Typical values are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C.

‡ Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, I<sub>OS</sub> tests should be performed last.

§ Per TTL-driven input (V<sub>IN</sub> = 3.4 V); all other inputs at V<sub>CC</sub> or GND

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	CY54FCT827T			CY74FCT827T			UNIT
					MIN	TYP†	MAX	
$I_{CCD}$ †	$V_{CC} = 5.5$ V, One input switching at 50% duty cycle, Outputs open, $\overline{OE}_1$ or $\overline{OE}_2 = GND$ , $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V		0.06	0.12				mA/MHz
	$V_{CC} = 5.25$ V, One input switching at 50% duty cycle, Outputs open, $\overline{OE}_1$ or $\overline{OE}_2 = GND$ , $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V					0.06	0.12	
$I_C$ #	$V_{CC} = 5.5$ V, Outputs open, $\overline{OE}_1$ or $\overline{OE}_2 = GND$	One bit switching at $f_1 = 10$ MHz	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V	0.7	1.4			mA
		at 50% duty cycle	$V_{IN} = 3.4$ V or GND	1	2.4			
		10 bits switching at $f_1 = 2.5$ MHz	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V	1.6	3.2			
		at 50% duty cycle	$V_{IN} = 3.4$ V or GND	4.1	13.2			
	$V_{CC} = 5.25$ V, Outputs open, $\overline{OE}_1$ or $\overline{OE}_2 = GND$	One bit switching at $f_1 = 10$ MHz	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V			0.7	1.4	
		at 50% duty cycle	$V_{IN} = 3.4$ V or GND			1	2.4	
		10 bits switching at $f_1 = 2.5$ MHz	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V			1.6	3.2	
		at 50% duty cycle	$V_{IN} = 3.4$ V or GND			4.1	13.2	
$C_i$				5	10	5	10	pF
$C_o$				9	12	9	12	pF

† This parameter is derived for use in total power-supply calculations.

$$\# I_C = I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD} (f_0/2 + f_1 \times N_1)$$

Where:

$I_C$  = Total supply current

$I_{CC}$  = Power-supply current with CMOS input levels

$\Delta I_{CC}$  = Power-supply current for a TTL high input ( $V_{IN} = 3.4$  V)

$D_H$  = Duty cycle for TTL inputs high

$N_T$  = Number of TTL inputs at  $D_H$

$I_{CCD}$  = Dynamic current caused by an input transition pair (HLH or LHL)

$f_0$  = Clock frequency for registered devices, otherwise zero

$f_1$  = Input signal frequency

$N_1$  = Number of inputs changing at  $f_1$

All currents are in milliamperes and all frequencies are in megahertz.

|| Values for these conditions are examples of the  $I_{CC}$  formula.

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**switching characteristics over operating free-air temperature range (see Figure 1)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST LOAD	CY54FCT827AT		CY74FCT827AT		CY74FCT827CT		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	D	Y	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	1.5	9	1.5	8	1.5	4.4	ns
t <sub>PHL</sub>				1.5	9	1.5	8	1.5	4.4	
t <sub>PLH</sub>	D	Y	C <sub>L</sub> = 300 pF, R <sub>L</sub> = 500 Ω	1.5	17	1.5	15	1.5	10	ns
t <sub>PHL</sub>				1.5	17	1.5	15	1.5	10	
t <sub>PZH</sub>	$\overline{OE}$	Y	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	1.5	13	1.5	12	1.5	7	ns
t <sub>PZL</sub>				1.5	13	1.5	12	1.5	7	
t <sub>PZH</sub>	$\overline{OE}$	Y	C <sub>L</sub> = 300 pF, R <sub>L</sub> = 500 Ω	1.5	25	1.5	23	1.5	14	ns
t <sub>PZL</sub>				1.5	25	1.5	23	1.5	14	
t <sub>PHZ</sub>	$\overline{OE}$	Y	C <sub>L</sub> = 5 pF, R <sub>L</sub> = 500 Ω	1.5	9	1.5	9	1.5	5.7	ns
t <sub>PHL</sub>				1.5	9	1.5	9	1.5	5.7	
t <sub>PHZ</sub>	$\overline{OE}$	Y	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	1.5	10	1.5	10	1.5	6	ns
t <sub>PHL</sub>				1.5	10	1.5	10	1.5	6	

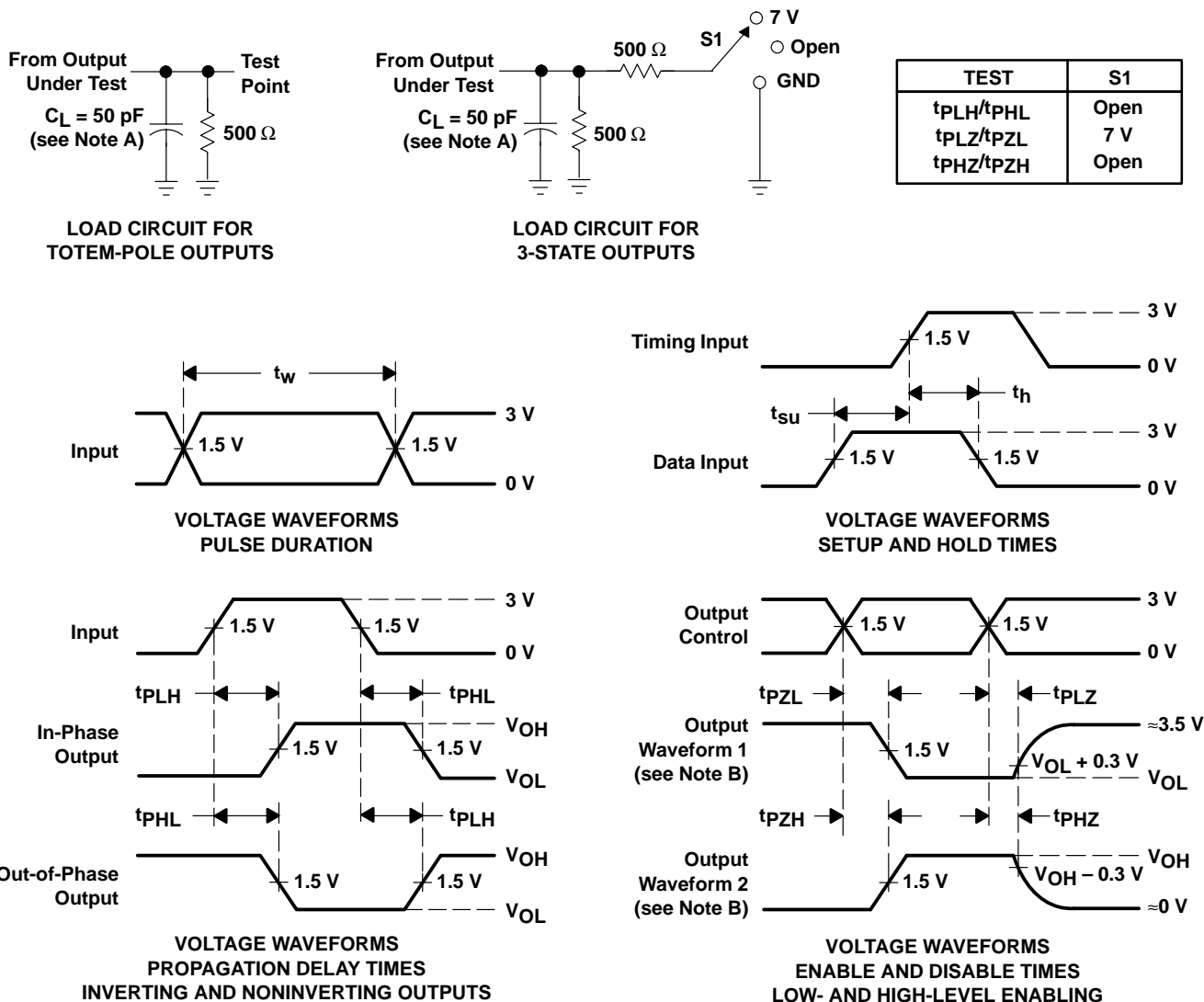
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## 10-BIT BUFFERS

### WITH 3-STATE OUTPUTS

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#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A.  $C_L$  includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

## PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">5962-9224701M3A</a>	Active	Production	LCCC (FK)   28	42   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9224701M3A
<a href="#">CY74FCT827ATQCT</a>	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT827A
CY74FCT827ATQCT.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT827A
<a href="#">CY74FCT827ATSOC</a>	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827A
CY74FCT827ATSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827A
<a href="#">CY74FCT827ATSOCT</a>	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827A
CY74FCT827ATSOCT.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827A
<a href="#">CY74FCT827CTQCT</a>	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT827C
CY74FCT827CTQCT.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT827C
<a href="#">CY74FCT827CTSOC</a>	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827C
CY74FCT827CTSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827C
<a href="#">CY74FCT827CTSOCT</a>	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827C
CY74FCT827CTSOCT.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT827C

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

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<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT827ATQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT827ATSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CY74FCT827CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT827CTSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT827ATQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT827ATSOCT	SOIC	DW	24	2000	350.0	350.0	43.0
CY74FCT827CTQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT827CTSOCT	SOIC	DW	24	2000	350.0	350.0	43.0

## TUBE



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
CY74FCT827ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT827ATSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT827CTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT827CTSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

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